SEMICONDUCTOR

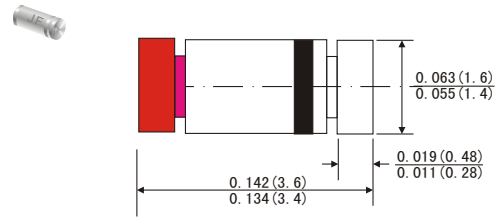
LL29

SMALL SIGNAL SCHOTTKY DIODES

FEATURES

- Metal-on-silicon junction
- Low turn-on voltage
- Ultrafast switching speed
- Primarily intended for high level UHF detection and pulse applications with broad dynamic range
- The diode is also available in the DO-35 case with type designation BAT29.
- High temperature soldering guaranteed: 260℃/10 seconds at terminals
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

MiniMELF



Dimensions in inches and (millimeters)

MECHANICAL DATA

- *Case*: MiniMELF glass case(SOD-80)
- Polarity: Color band denotes cathode end
- *Weight*: Approx. 0.05 gram

ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units
Peak Reverse Voltage	V_{RRM}	5	V
Forward Continuous Current	I_F	30	mA
Surge non repetitive Forward current $t_p \leqslant 1s$	I_{FSM}	2.0	A
Junction and Storage temperature range	T_{STG}	-55 to+150	℃
Junction temperature	T_J	125	℃

ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	Unis
Reverse breakover voltage at I_R=100μA	V_R	5			V V
Leakage current at V_R=1V	I_R			50	nA
Forward voltage drop at I_F=10mA Test pulse:$t_p \leqslant 300\mu s$ $\delta < 2\%$	V_F			0.55	V
Junction Capacitance at V_R=0V ,f=1GHz	C_J			1.0	pF
Thermal resistance	$R_{\theta JA}$			400	K/W

JINAN JINGHENG CO., LTD. NO.51 HEPING ROAD JINAN P.R. CHINA TEL:86-531-86943657 FAX:86-531-86947096 WWW.JIFUSEMICON.COM

RATINGS AND CHARACTERISTIC CURVES LL29

Figure 1. forward current versus forward voltage (typical values)

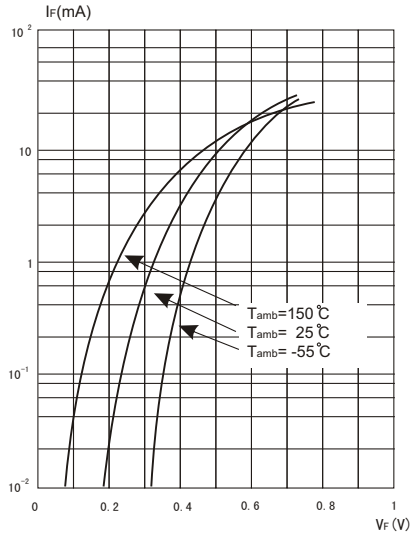


Figure 2. Capacitance CJ versus reverse applied voltage VR (typical values)

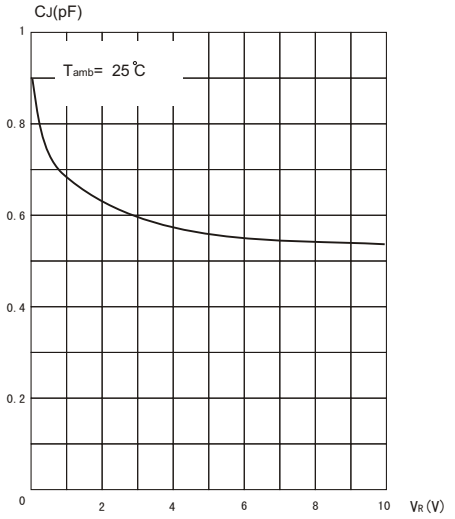


Figure 3.Reverse current versus ambient temperature

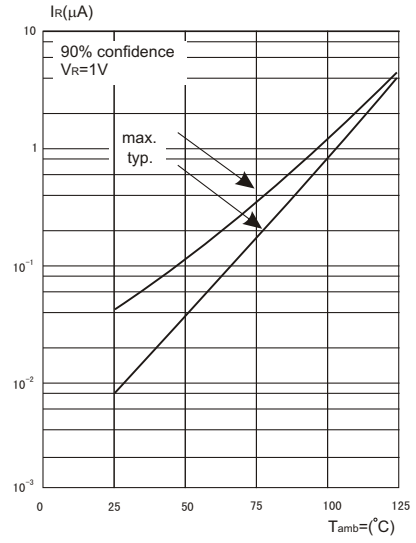
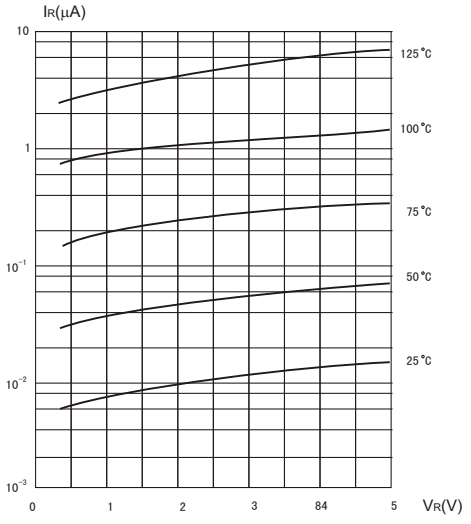


Figure 4.Reverse current versus continuous Reverse voltage(typical values)



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